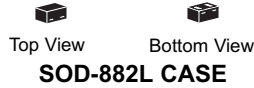




CFSH2-4L
SURFACE MOUNT
SILICON SCHOTTKY DIODE



CentralTM

Semiconductor Corp.

DESCRIPTION:

The Central Semiconductor CFSH2-4L is a high quality Schottky Diode designed for applications where ultra small size and power dissipation are prime requirements. Packaged in a Tiny Leadless PackageTM (TLPTM), this component provides performance characteristics suitable for the most demanding size constrained applications.

MARKING CODE: N

FEATURES:

- Device is **Halogen Free** by design
- Current ($I_O=200mA$)
- Low Forward Voltage Drop ($V_F=0.53V$ TYP @ 200mA)
- Low Reverse Current (350nA TYP @ 40V)
- Small TLPTM, 1mm x 0.6mm x 0.4mm, ultra low profile, Leadless Surface Mount package.

APPLICATIONS:

- DC / DC Converters
- Voltage Clamping
- Protection Circuits
- Battery powered devices including Cell Phones, Digital Cameras, Pagers, PDAs, Laptop Computers, etc.

MAXIMUM RATINGS: ($T_A=25^\circ C$)

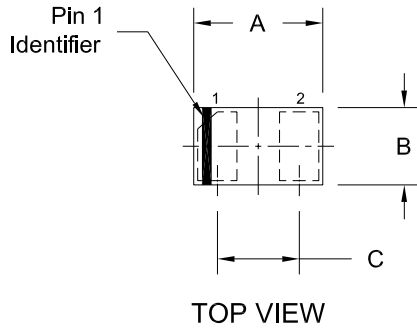
	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	40	V
Average Forward Current	I_O	200	mA
Forward Surge Current, $t_p=8.3ms$	I_{FSM}	1.0	A
Power Dissipation	P_D	100	mW
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +125	$^\circ C$
Thermal Resistance	θ_{JA}	1000	$^\circ C/W$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ C$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_R	$V_R=10V$		0.08	1.0	μA
I_R	$V_R=40V$		0.35	2.0	μA
BV_R	$I_R=10\mu A$	40			V
V_F	$I_F=10mA$		0.33	0.45	V
V_F	$I_F=100mA$			0.52	V
V_F	$I_F=200mA$		0.53	0.60	V
C_T	$V_R = 4.0V, f=1.0$ MHz		7.0	10	pF
t_{rr}	$I_F=I_R=10mA, I_{rr}=1.0mA, R_L=100\Omega$		5.0		ns

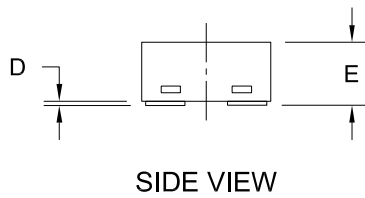
R1 (12-September 2007)

SOD-882L CASE - MECHANICAL OUTLINE



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.037	0.041	0.95	1.05
B	0.022	0.026	0.55	0.65
C	0.026		0.65	
D	0.000	0.002	0.00	0.05
E	0.012	0.016	0.30	0.40
F	0.018	0.022	0.45	0.55
G	0.008	0.012	0.20	0.30

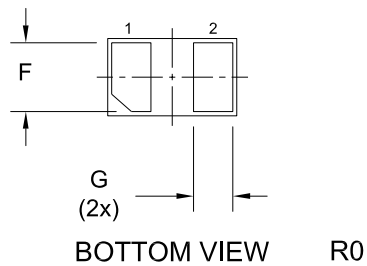
SOD-882L (REV:R0)



LEAD CODE:

- 1) CATHODE
- 2) ANODE

MARKING CODE: N



R1 (12-September 2007)